TOSHIBA Transistor Silicon PNP Epitaxial Type

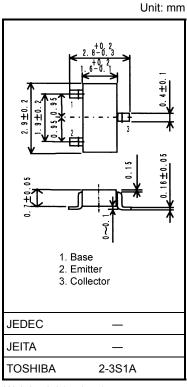
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High-Speed Switching Applications DC-DC Converter Applications Strobe Applications

- High DC current gain: $h_{FE} = 200 \text{ to } 500 \text{ (I}_{C} = -0.5 \text{ A)}$
- Low collector-emitter saturation voltage: $V_{CE (sat)} = -0.2 \text{ V (max)}$
- High-speed switching: tf = 90 ns (typ.)

Maximum Ratings (Ta = 25°C)

| Characteristics | | Symbol | Rating | Unit | |
|-----------------------------|----------|------------------|------------|------|--|
| Collector-base voltage | | V _{CBO} | -50 | V | |
| Collector-emitter voltage | | V _{CEO} | -50 | V | |
| Emitter-base voltage | | V _{EBO} | -7 | V | |
| Collector current | DC | IC | -2.0 | Α | |
| | Pulse | I _{CP} | -3.5 | | |
| Base current | | ΙΒ | -200 | mA | |
| Collector power dissipation | t = 10 s | PC | 1000 | mW | |
| | DC | (Note 1) | 625 | | |
| Junction temperature | | Tj | 150 | °C | |
| Storage temperature range | | T _{stg} | −55 to 150 | °C | |



Weight: 0.01 g (typ.)

Note 1: Mounted on an FR4 board (glass epoxy, 1.6 mm thick, Cu area: 645 mm²)

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Electrical Characteristics (Ta = 25°C)

| Characteristics | | Symbol | Test Condition | Min | Тур. | Max | Unit | |
|--------------------------------------|--------------|-----------------------|--|-----|------|------|------|--|
| Collector cut-off current | | I _{CBO} | $V_{CB} = -50 \text{ V}, I_E = 0$ | _ | _ | -100 | nA | |
| Emitter cut-off current | | I _{EBO} | $V_{EB} = -7 \text{ V}, I_{C} = 0$ | _ | _ | -100 | nA | |
| Collector-emitter breakdown voltage | | V (BR) CEO | I _C = −10 mA, I _B = 0 | -50 | _ | _ | V | |
| DC current gain | | h _{FE} (1) | $V_{CE} = -2 \text{ V}, I_{C} = -0.3 \text{ A}$ | 200 | _ | 500 | | |
| | | h _{FE} (2) | V _{CE} = −2 V, I _C = −1.0 A | 100 | _ | _ | | |
| Collector-emitter saturation voltage | | V _{CE (sat)} | I _C = −1.0 A, I _B = −0.033 A | _ | _ | -0.2 | V | |
| Base-emitter saturation voltage | | V _{BE} (sat) | I _C = −1.0 A, I _B = −0.033 A | _ | _ | -1.1 | V | |
| Collector output capacitance | | C _{ob} | V _{CB} = −10 V, I _E = 0, f = 1 MHz | _ | 20 | _ | pF | |
| Switching time | Rise time | t _r | See Figure 1 circuit diagram. | _ | 60 | _ | | |
| | Storage time | t _{stg} | $V_{CC} \approx -30 \text{ V}, R_L = 30 \Omega$ | _ | 250 | _ | ns | |
| | Fall time | t _f | $-I_{B1} = I_{B2} = -33 \text{ mA}$ | _ | 90 | _ | | |

Marking

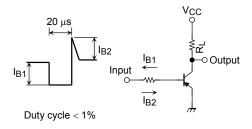
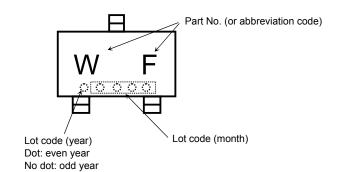
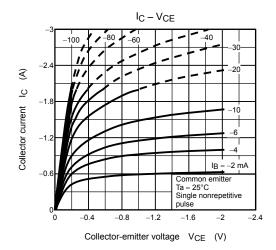
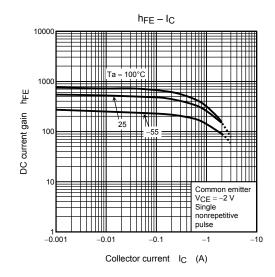
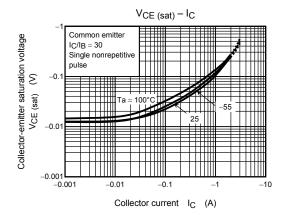


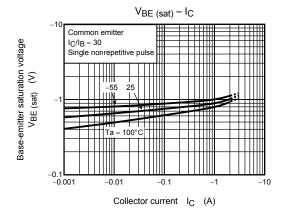
Figure 1 Switching Time Test Circuit & Timing Chart

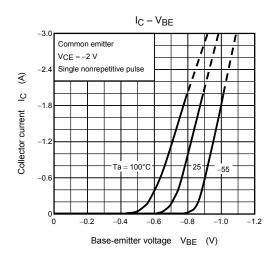




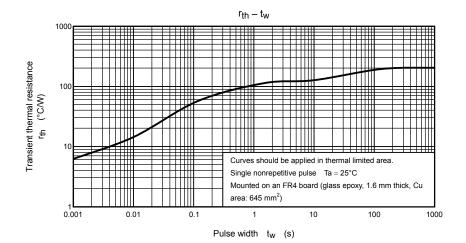


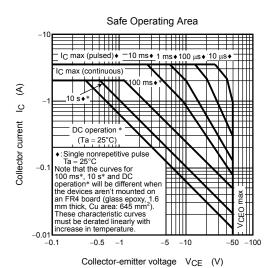






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